

FCI7N60

N-Channel SuperFET® MOSFET

600 V, 7 A, 600 mΩ

Features

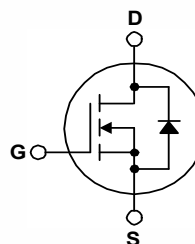
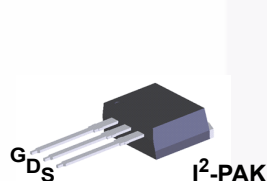
- 650V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 530\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 23\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 60\text{ pF}$)
- 100% Avalanche Tested
- RoHS compliant

Application

- Lighting
- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCI7N60	Unit
V_{DSS}	Drain to Source Voltage	600	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	7
		- Continuous ($T_C = 100^\circ\text{C}$)	4.4
I_{DM}	Drain Current	- Pulsed (Note 1)	21
V_{GSS}	Gate to Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	230
I_{AR}	Avalanche Current	(Note 1)	7
E_{AR}	Repetitive Avalanche Energy	(Note 1)	8.3
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	83
		- Derate Above 25°C	0.67
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FCI7N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCI7N60	FCI7N60	I ² -PAK	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}, T_C = 25^\circ\text{C}$	600	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}, T_C = 150^\circ\text{C}$	-	650	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	-	0.6	-	V/ $^\circ\text{C}$
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 7\text{ A}$	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	-	-	10	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$	-	0.53	0.6	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 3.5\text{ A}$	-	6	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	-	710	920	pF
C_{oss}	Output Capacitance		-	380	500	pF
C_{rss}	Reverse Transfer Capacitance		-	34	-	pF
C_{oss}	Output Capacitance	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	22	29	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	60	-	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 7\text{ A}, V_{GS} = 10\text{ V}, R_G = 25\text{ }\Omega$ (Note 4)	-	35	80	ns
t_r	Turn-On Rise Time		-	55	120	ns
$t_{d(off)}$	Turn-Off Delay Time		-	75	160	ns
t_f	Turn-Off Fall Time		-	32	75	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 480\text{ V}, I_D = 7\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	-	23	30	nC
Q_{gs}	Gate to Source Gate Charge		-	4.2	5.5	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	11.5	-	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	7	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	21	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 7 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 7 A, dI _F /dt = 100 A/μs	-	360	-	ns
Q _{rr}	Reverse Recovery Charge		-	4.5	-	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $I_{AS} = 3.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 7\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

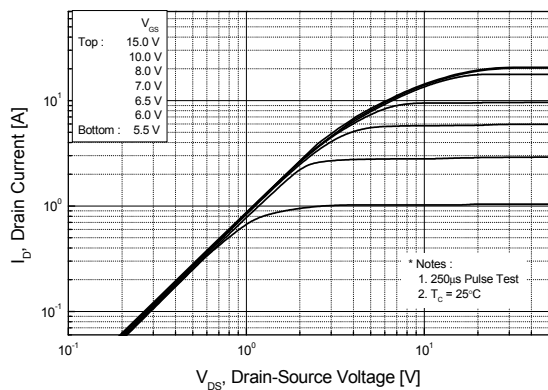


Figure 2. Transfer Characteristics

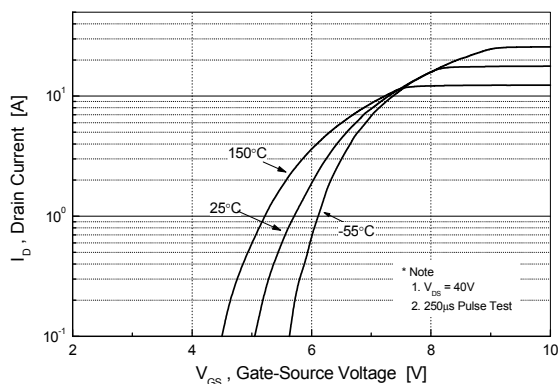


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

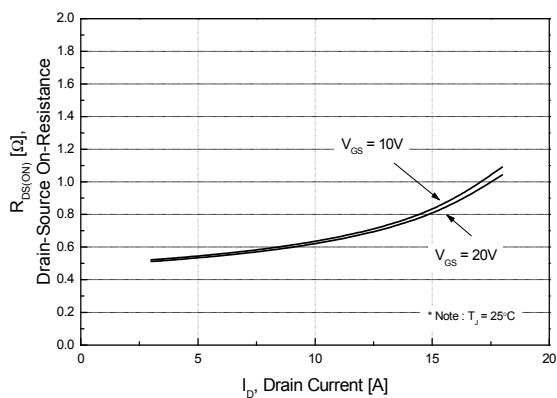


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

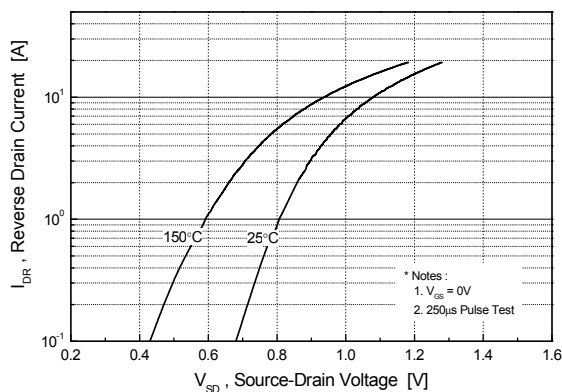


Figure 5. Capacitance Characteristics

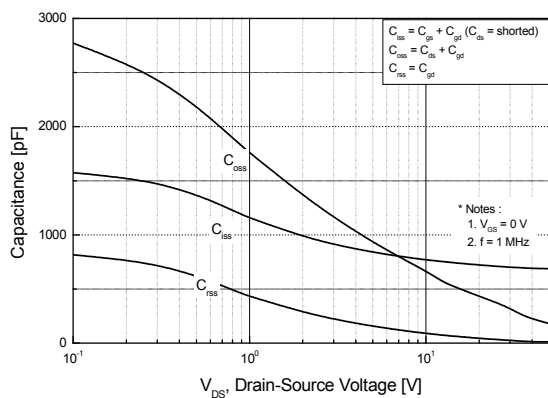
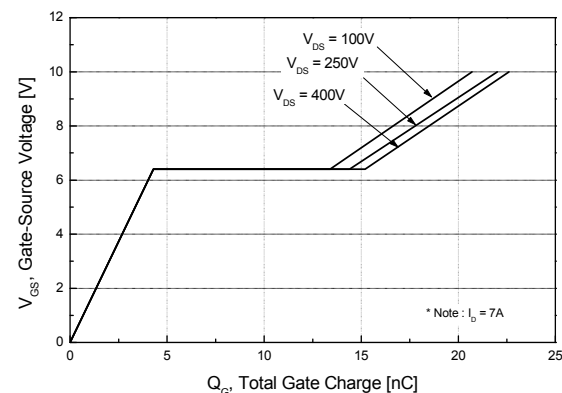


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

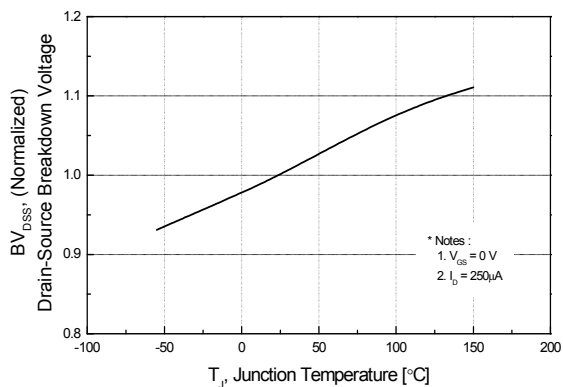


Figure 8. On-Resistance Variation vs. Temperature

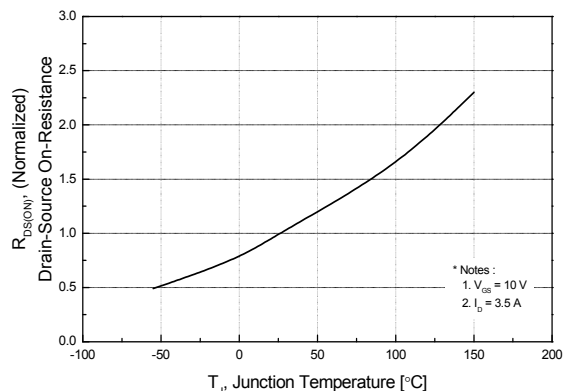


Figure 9. Maximum Safe Operating Area

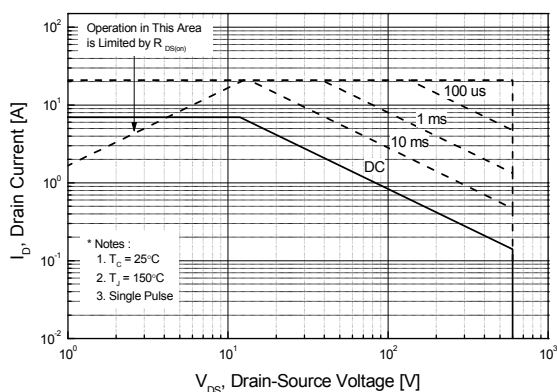


Figure 10. Maximum Drain Current vs. Case Temperature

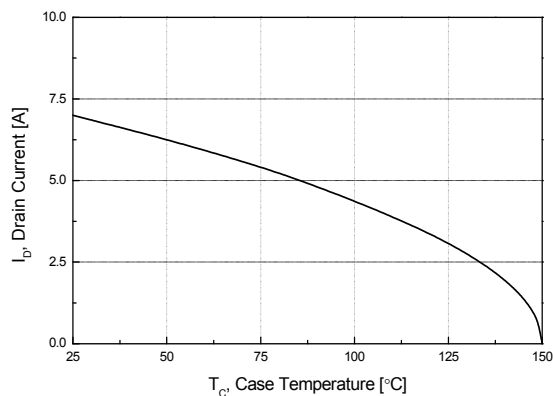
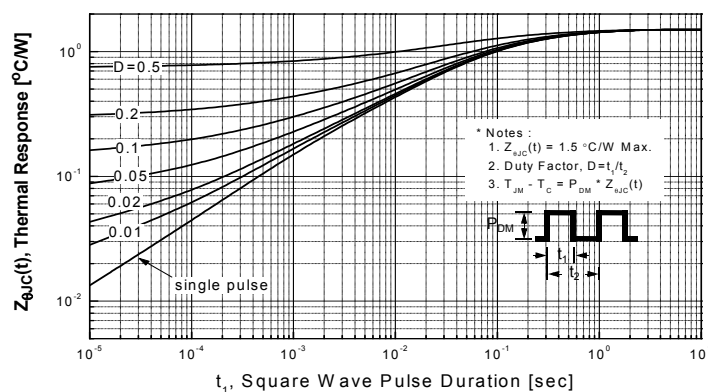


Figure 11. Transient Thermal Response Curve



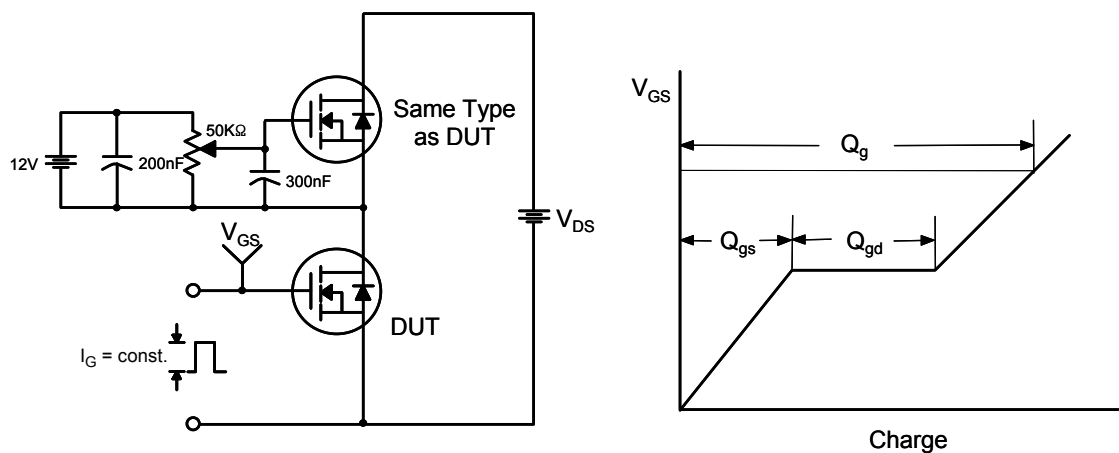


Figure 12. Gate Charge Test Circuit & Waveform

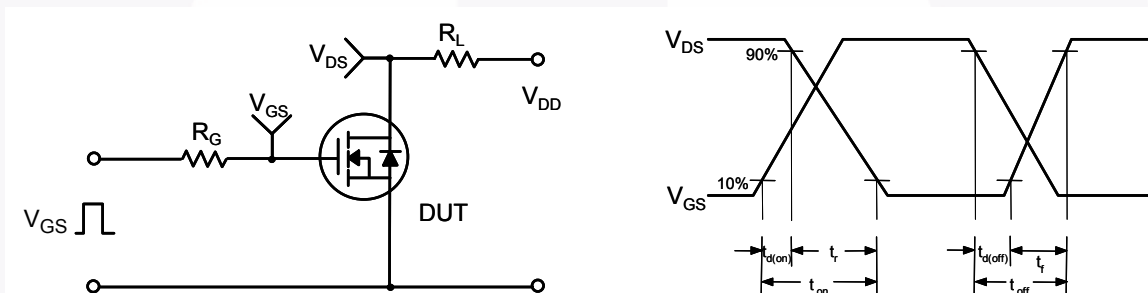


Figure 13. Resistive Switching Test Circuit & Waveforms

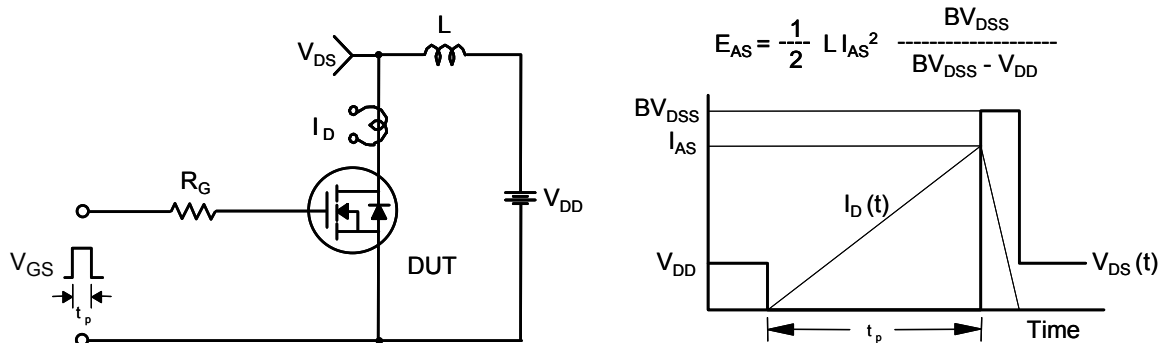
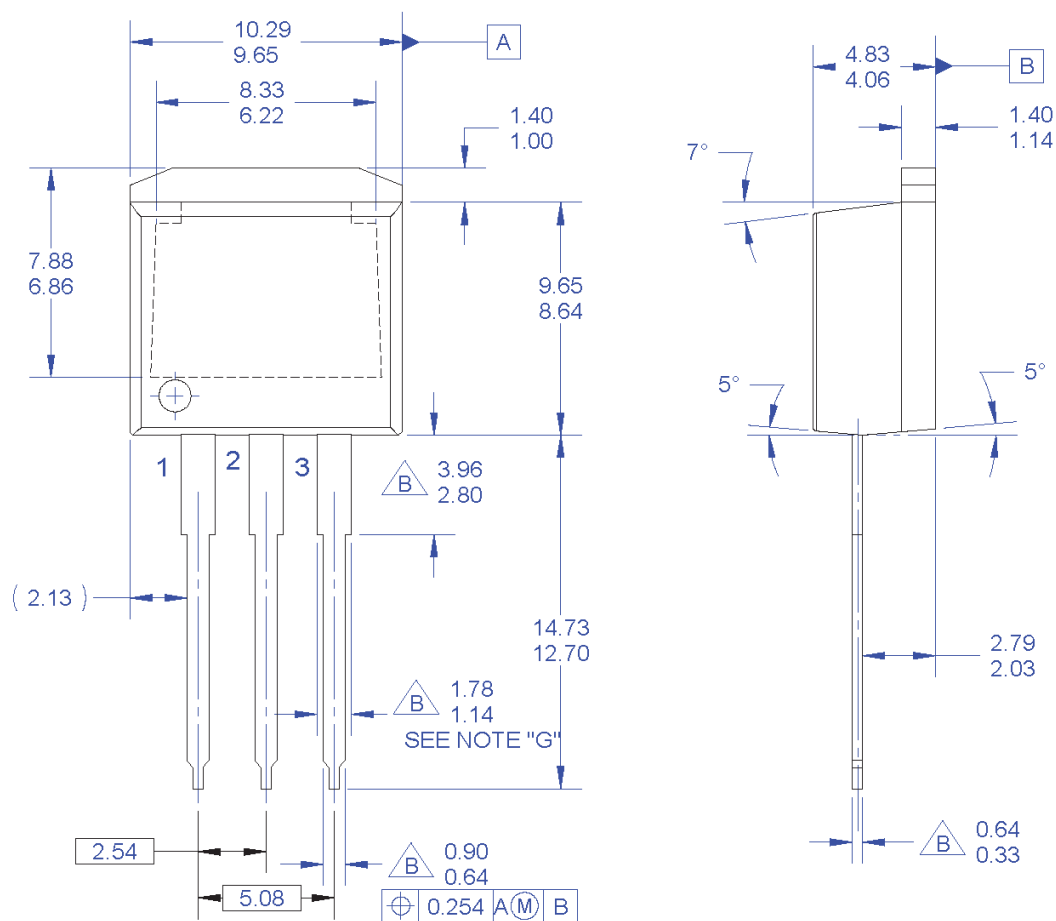


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO TO262 JEDEC VARIATION AA.
- B. DOES NOT COMPLY JEDEC STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ANSI Y14.5-1994.
- F. LOCATION OF PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF PACKAGE)
- G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.
- H. DRAWING FILE NAME: TO262A03REV5

Figure 16. TO262 (I²PAK), Molded, 3-Lead, Jedec Variation AA

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

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